

BF959

VHF Transistor

NPN Silicon



ON Semiconductor™

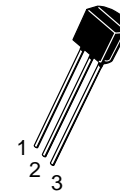
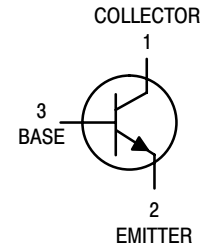
<http://onsemi.com>

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	20	Vdc
Collector–Base Voltage	V_{CBO}	30	Vdc
Emitter–Base Voltage	V_{EBO}	3.0	Vdc
Collector Current – Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	°C

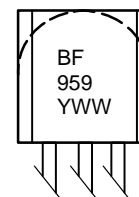
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W



TO-92
CASE 29
STYLE 21

MARKING DIAGRAM



Y = Year
W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
BF959	TO-92	5000 Units/Box
BF959ZL1	TO-92	2000/Ammo Pack
BF959RL1	TO-92	2000 Units/Box

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	20	–	–	Vdc
Collector–Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	30	–	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\ \mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	3.0	–	–	Vdc
Collector Cutoff Current ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	–	100	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 20\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	35 40	– –	– –	–
Collector–Emitter Saturation Voltage ($I_C = 30\text{ mA}$, $I_B = 2.0\text{ mA}$)	$V_{CE(sat)}$	–	–	1.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 30\text{ mA}$, $I_B = 2.0\text{ mA}$)	$V_{BE(sat)}$	–	–	1.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 20\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$) ($I_C = 30\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	700 600	– –	– –	MHz
Common Emitter Feedback Capacitance ($V_{CB} = 10\text{ Vdc}$, $P_f = 0$, $f = 10\text{ MHz}$)	C_{re}	–	0.65	–	pF
Noise Figure ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ V}$, $R_S = 50\ \Omega$, $f = 200\text{ MHz}$)	N_f	–	3.0	–	dB

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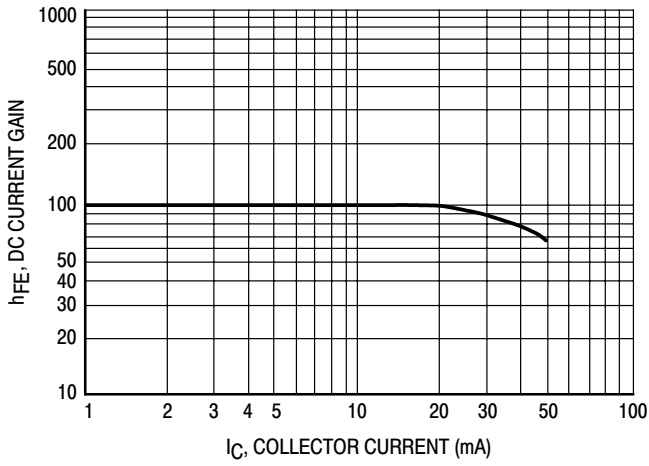


Figure 1. h_{FE} at 10 V

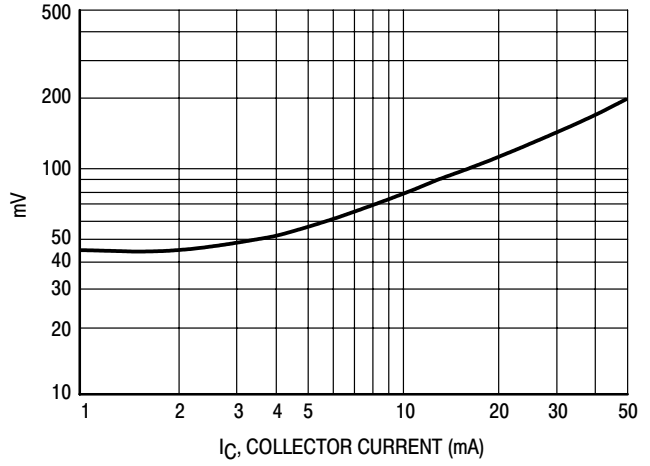


Figure 2. $V_{CE(sat)}$ at $I_C/I_B = 10$

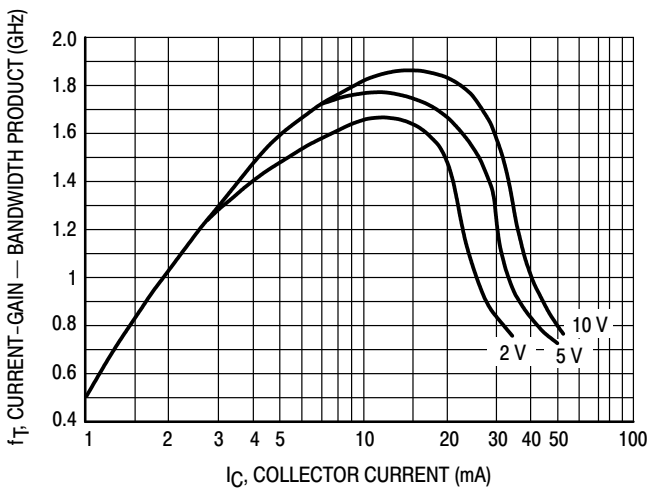


Figure 3. Current-Gain - Bandwidth Product

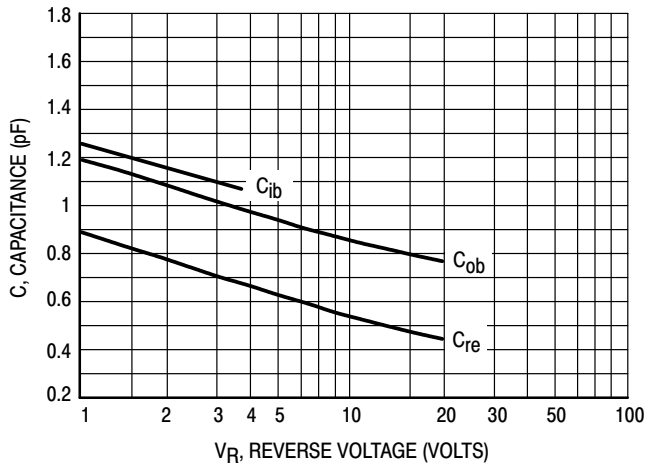


Figure 4. Capacitances

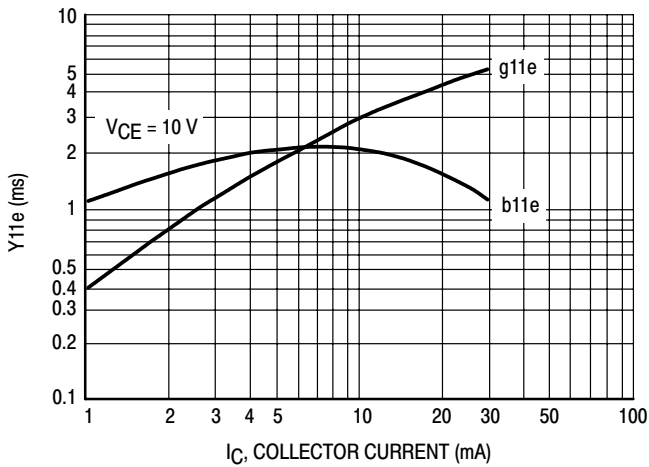


Figure 5. Input Impedance at 30 MHz

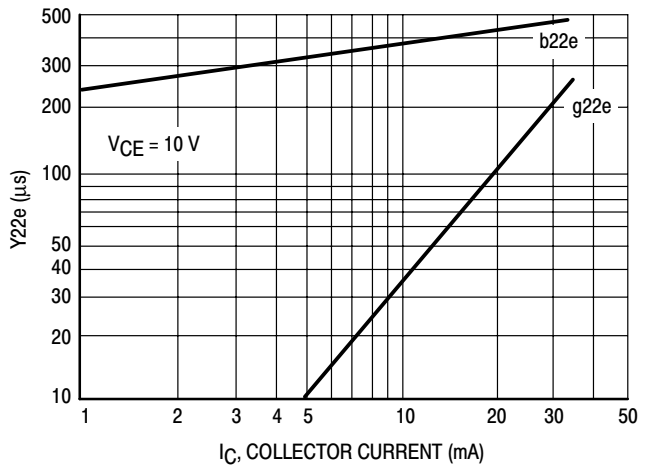
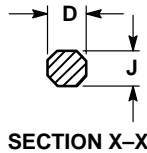
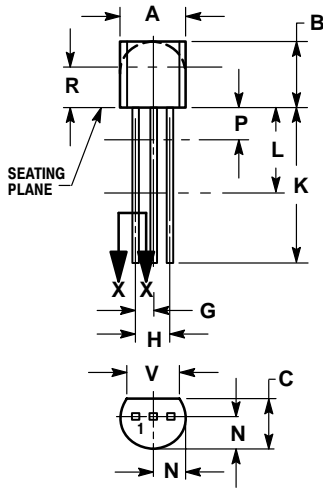


Figure 6. Output Impedance at 30 MHz

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PACKAGE DIMENSIONS

TO-92
TO-226AA
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 21:

1. COLLECTOR
2. EMITTER
3. BASE

STYLE 14:

1. EMITTER
2. COLLECTOR
3. BASE

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